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April 2015

# FDD770N15A

## N-Channel PowerTrench<sup>®</sup> MOSFET

150 V, 18 A, 77 mΩ

### Features

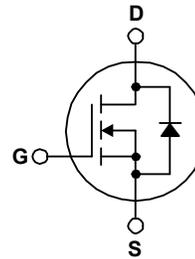
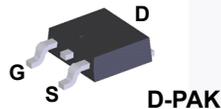
- $R_{DS(on)} = 61 \text{ m}\Omega$  (Typ.) @  $V_{GS} = 10 \text{ V}$ ,  $I_D = 12 \text{ A}$
- Fast Switching Speed
- Low Gate Charge
- High Performance Trench Technology for Extremely Low  $R_{DS(on)}$
- High Power and Current Handling Capability
- RoHS Compliant

### Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench<sup>®</sup> process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

### Applications

- DC to DC Converters
- Synchronous Rectification for Server / Telecom PSU
- Battery Charger
- AC motor drives and Uninterruptible Power Supplies
- Off-line UPS



### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FDD770N15A	Unit
$V_{DSS}$	Drain to Source Voltage	150	V
$V_{GSS}$	Gate to Source Voltage	- DC	$\pm 20$
		- AC (f > 1 Hz)	$\pm 30$
$I_D$	Drain Current	- Continuous ( $T_C = 25^\circ\text{C}$ , Silicon Limited)	18
		- Continuous ( $T_C = 100^\circ\text{C}$ , Silicon Limited)	11.4
$I_{DM}$	Drain Current	- Pulsed (Note 1)	36
$E_{AS}$	Single Pulsed Avalanche Energy	(Note 2)	31.7
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	6.0
$P_D$	Power Dissipation	( $T_C = 25^\circ\text{C}$ )	56.8
		- Derate Above $25^\circ\text{C}$	0.46
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
$T_L$	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

### Thermal Characteristics

Symbol	Parameter	FDD770N15A	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	2.2	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	87	

FDD770N15A — N-Channel PowerTrench<sup>®</sup> MOSFET

## Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDD770N15A	FDD770N15A	DPAK	Tape and Reel	330 mm	16 mm	2500 units

## Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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### Off Characteristics

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250 \mu\text{A}, V_{GS} = 0 \text{ V}$	150	-	-	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$ , Referenced to $25^\circ\text{C}$	-	0.0824	-	$\text{V}/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 120 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	$\mu\text{A}$
		$V_{DS} = 120 \text{ V}, V_{GS} = 0 \text{ V}, T_C = 125^\circ\text{C}$	-	-	500	
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	$\pm 100$	nA

### On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu\text{A}$	2.0	-	4.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 12 \text{ A}$	-	61	77	$\text{m}\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 10 \text{ V}, I_D = 12 \text{ A}$	-	20	-	S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 75 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	575	765	pF
$C_{oss}$	Output Capacitance		-	64	85	pF
$C_{rSS}$	Reverse Transfer Capacitance		-	3.9	6	pF
$C_{oss(er)}$	Energy Related Output Capacitance	$V_{DS} = 75 \text{ V}, V_{GS} = 0 \text{ V}$	-	113	-	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	$V_{DS} = 75 \text{ V}, I_D = 12 \text{ A}, V_{GS} = 10 \text{ V}$	-	8.4	11	nC
$Q_{gs}$	Gate to Source Gate Charge		-	2.7	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge		-	1.8	-	nC
$V_{plateau}$	Gate Plateau Voltage		(Note 4)	-	5.7	-
$Q_{sync}$	Total Gate Charge Sync.	$V_{DS} = 0 \text{ V}, I_D = 6 \text{ A}$	-	6.9	-	nC
$Q_{oss}$	Output Charge	$V_{DS} = 37.5 \text{ V}, V_{GS} = 0 \text{ V}$	-	14	-	nC
ESR	Equivalent Series Resistance (G-S)	$f = 1 \text{ MHz}$	-	0.5	-	$\Omega$

### Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 75 \text{ V}, I_D = 12 \text{ A}, V_{GS} = 10 \text{ V}, R_G = 4.7 \Omega$	-	10.3	30.6	ns
$t_r$	Turn-On Rise Time		-	3.1	16.2	ns
$t_{d(off)}$	Turn-Off Delay Time		-	15.8	41.6	ns
$t_f$	Turn-Off Fall Time		(Note 4)	-	2.8	15.6

### Drain-Source Diode Characteristics

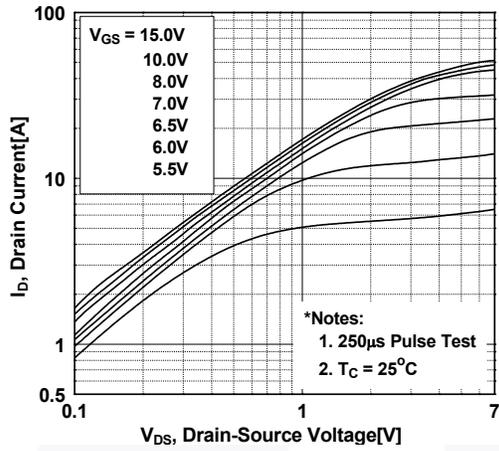
$I_S$	Maximum Continuous Drain to Source Diode Forward Current	-	-	18	A	
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current	-	-	36	A	
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{SD} = 12 \text{ A}$	-	-	1.25	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0 \text{ V}, V_{DD} = 75 \text{ V}, I_{SD} = 12 \text{ A}$	-	56.4	-	ns
$Q_{rr}$	Reverse Recovery Charge	$di_F/dt = 100 \text{ A}/\mu\text{s}$	-	109	-	nC

#### Notes:

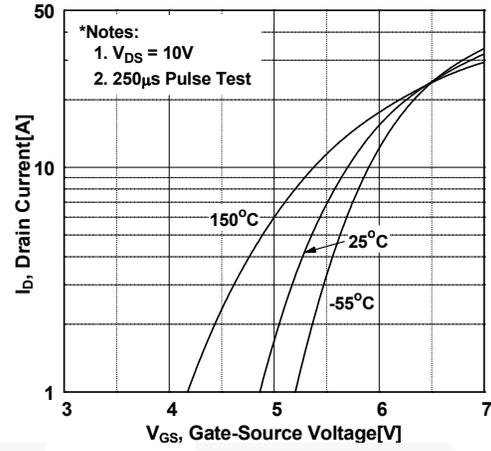
1. Repetitive rating; pulse-width limited by maximum junction temperature.
2.  $L = 3 \text{ mH}, I_{AS} = 4.6 \text{ A}$ , starting  $T_J = 25^\circ\text{C}$ .
3.  $I_{SD} \leq 12 \text{ A}, di/dt \leq 200 \text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$ , starting  $T_J = 25^\circ\text{C}$ .
4. Essentially independent of operating temperature typical characteristics.

## Typical Performance Characteristics

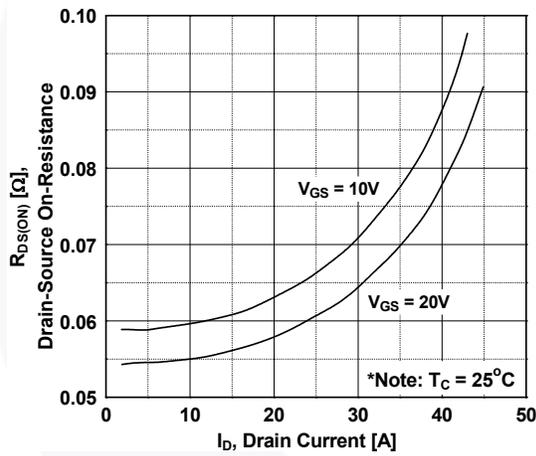
**Figure 1. On-Region Characteristics**



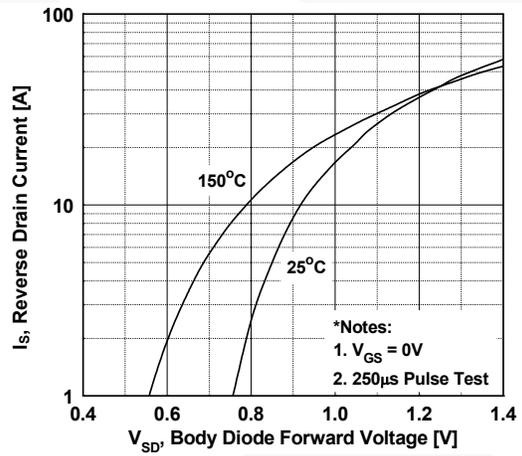
**Figure 2. Transfer Characteristics**



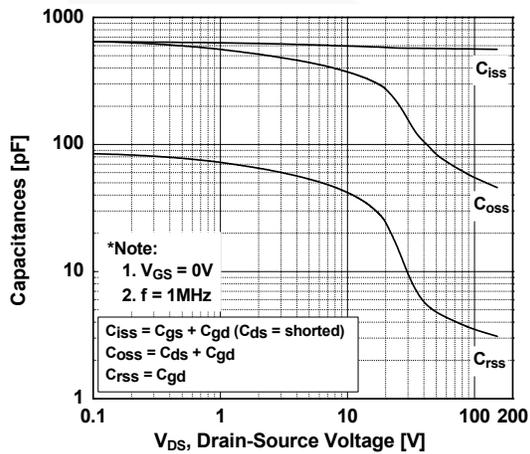
**Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage**



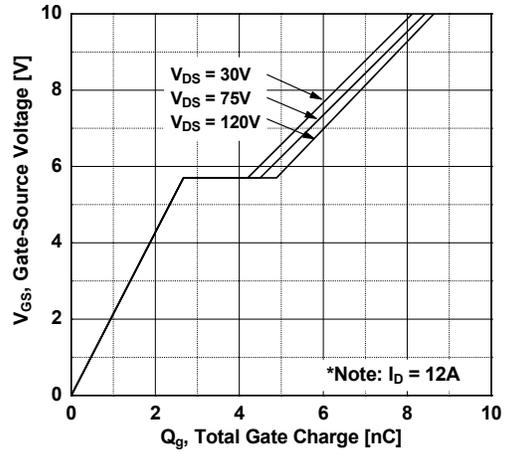
**Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature**



**Figure 5. Capacitance Characteristics**

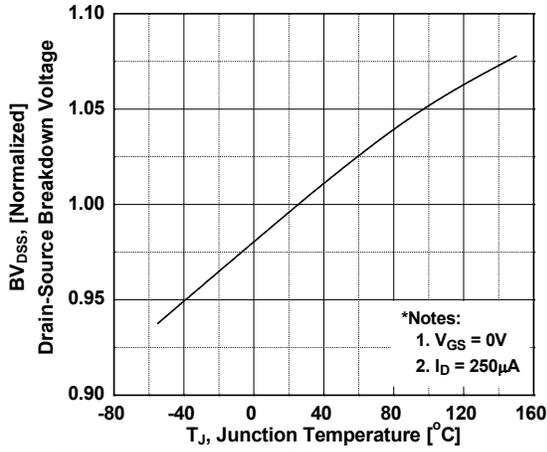


**Figure 6. Gate Charge Characteristics**

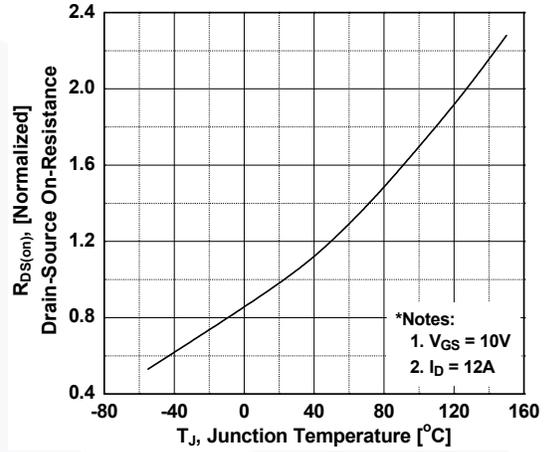


**Typical Performance Characteristics** (Continued)

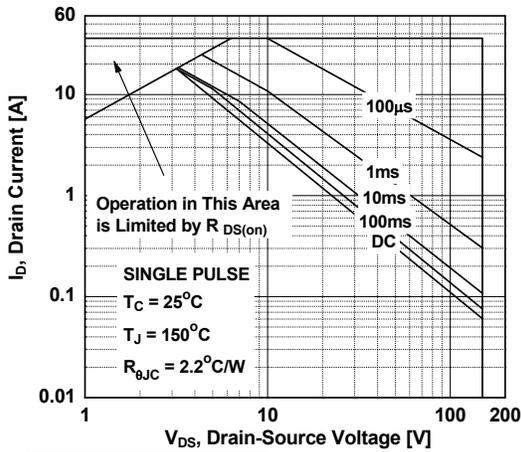
**Figure 7. Breakdown Voltage Variation vs. Temperature**



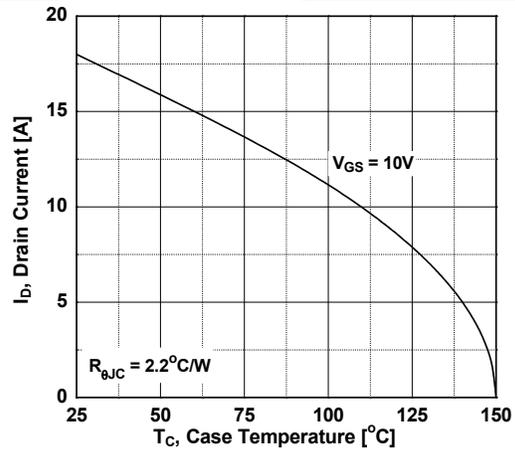
**Figure 8. On-Resistance Variation vs. Temperature**



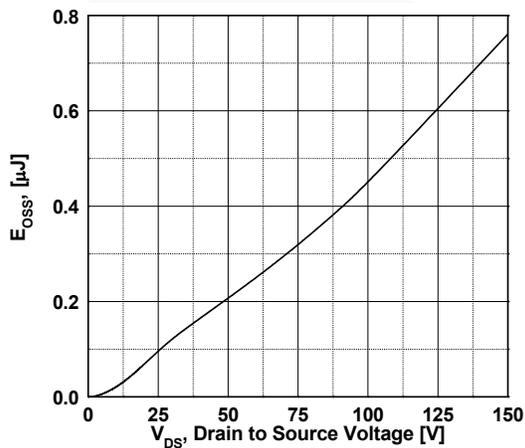
**Figure 9. Maximum Safe Operating Area**



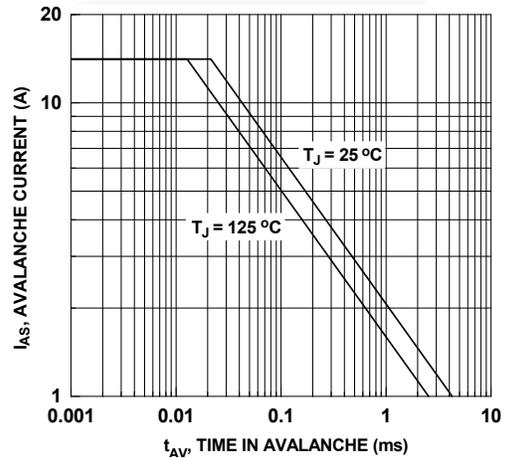
**Figure 10. Maximum Drain Current vs. Case Temperature**



**Figure 11. E\_oss vs. Drain to Source Voltage**

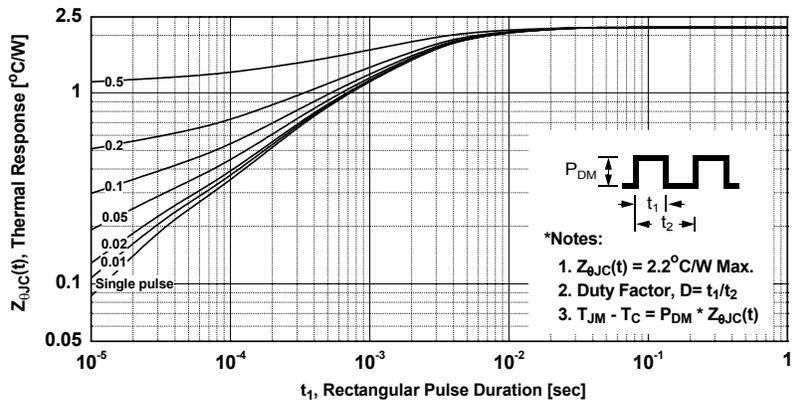


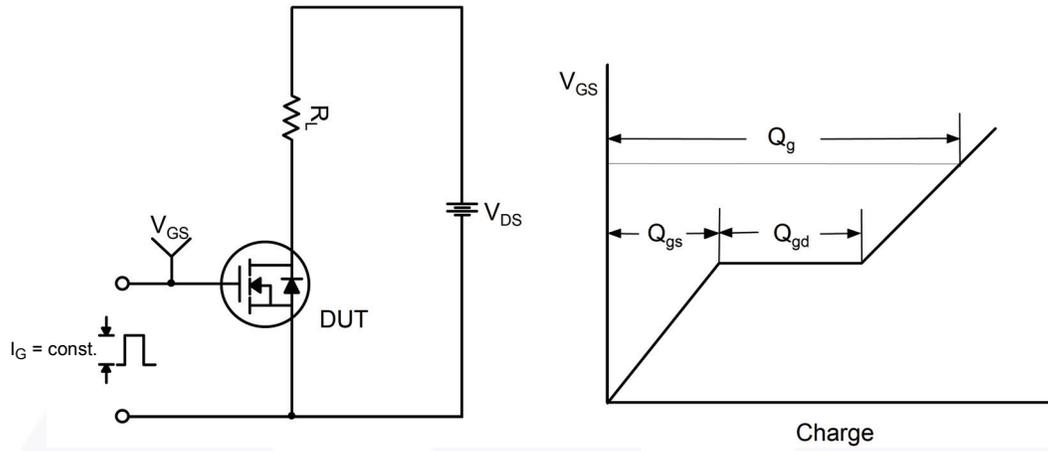
**Figure 12. Unclamped Inductive Switching Capability**



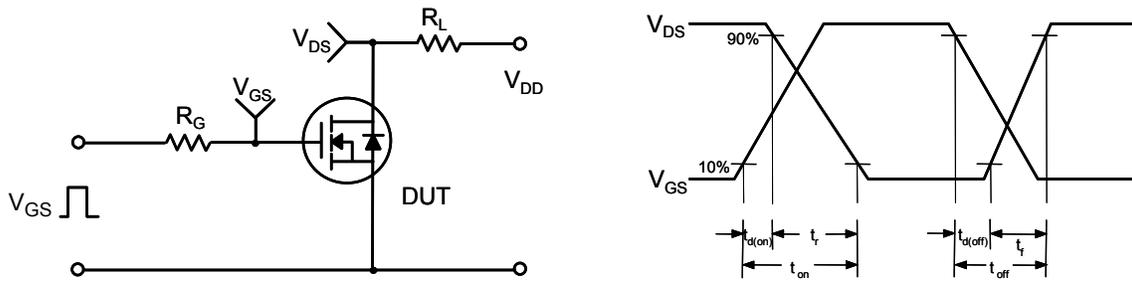
Typical Performance Characteristics (Continued)

Figure 13. Transient Thermal Response Curve

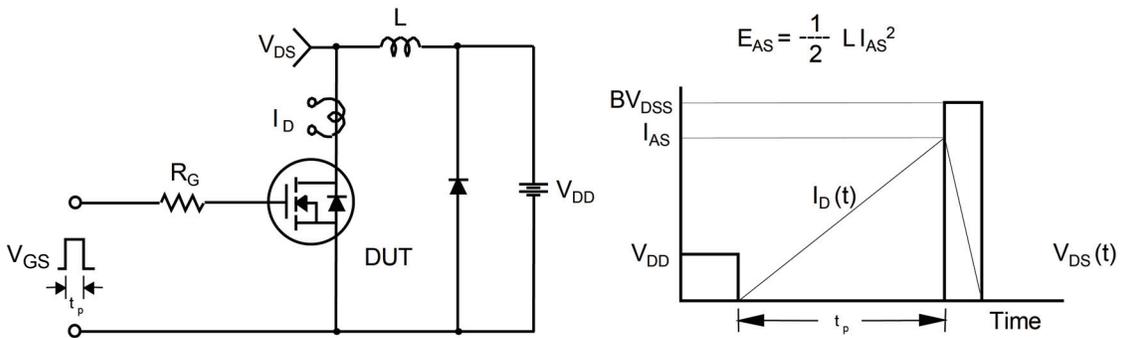




**Figure 14. Gate Charge Test Circuit & Waveform**



**Figure 15. Resistive Switching Test Circuit & Waveforms**



**Figure 16. Unclamped Inductive Switching Test Circuit & Waveforms**

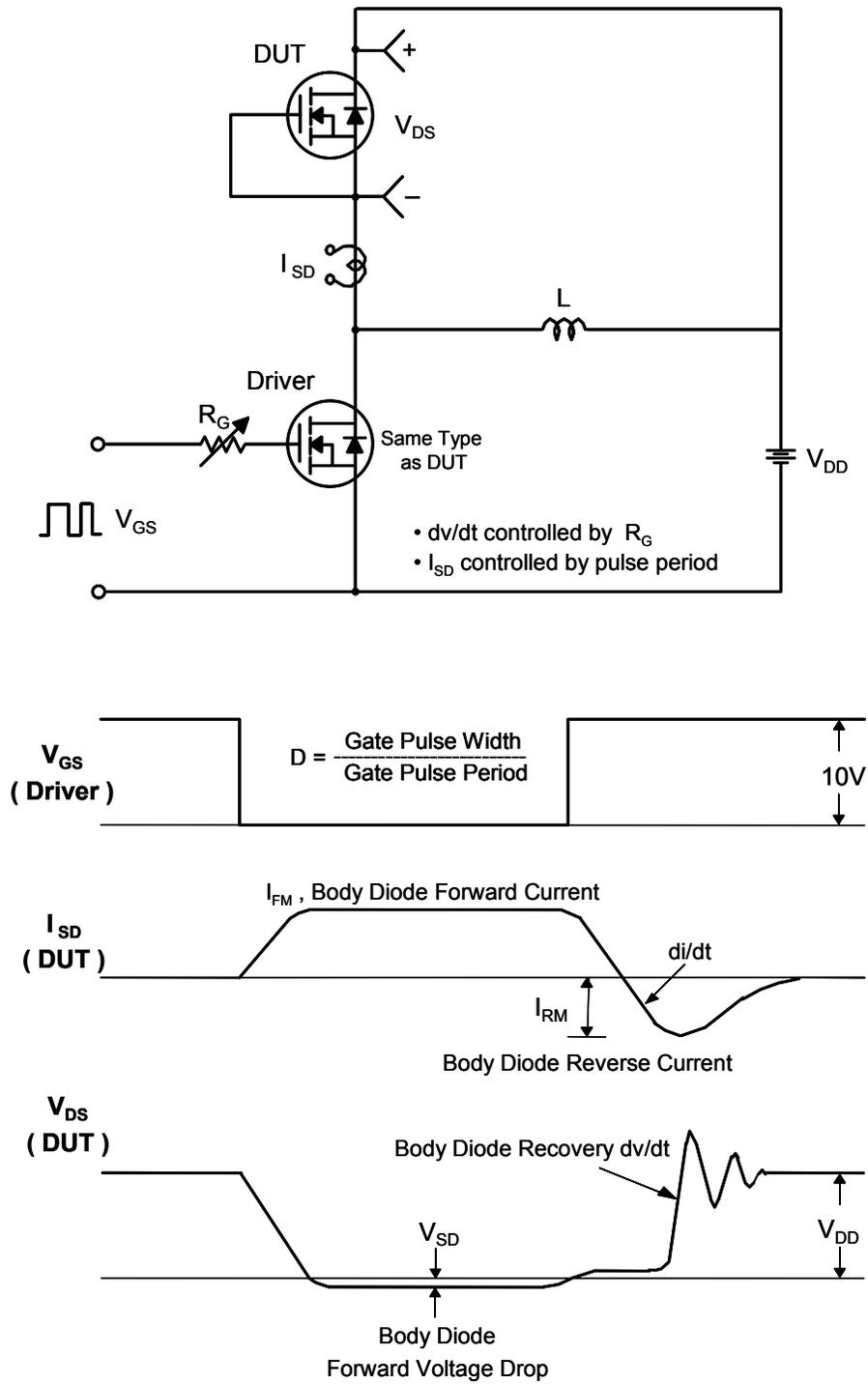


Figure 17. Peak Diode Recovery  $dv/dt$  Test Circuit & Waveforms

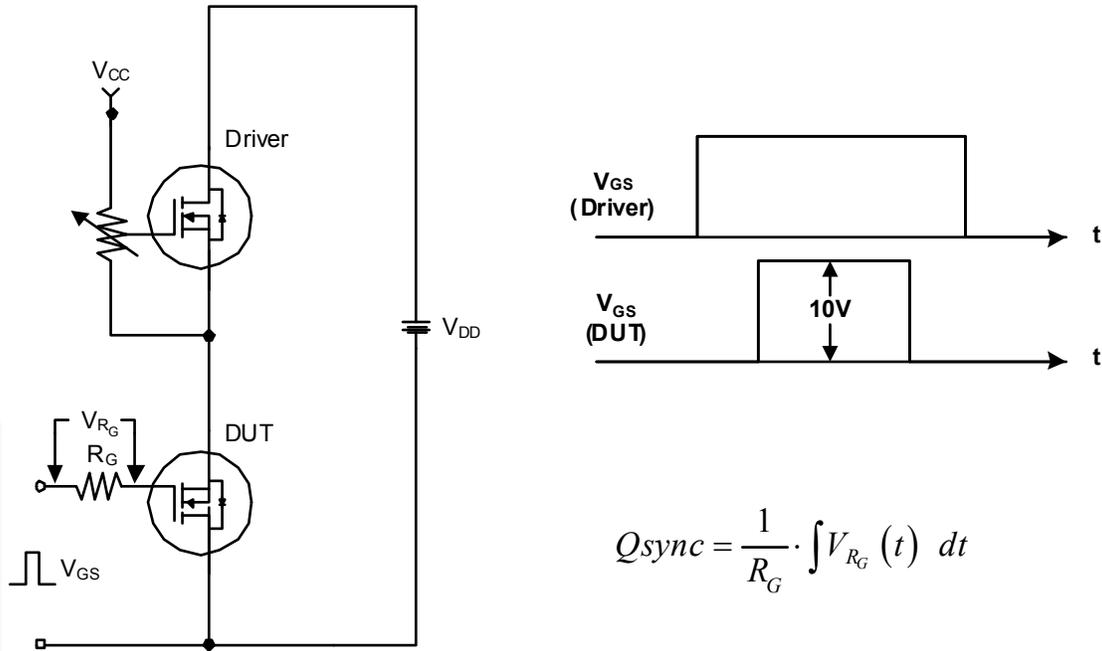
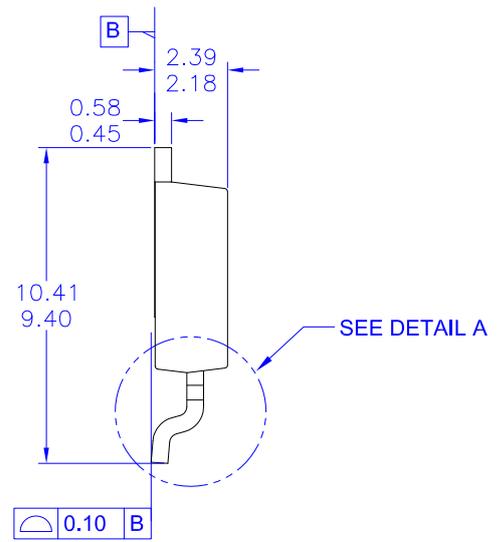
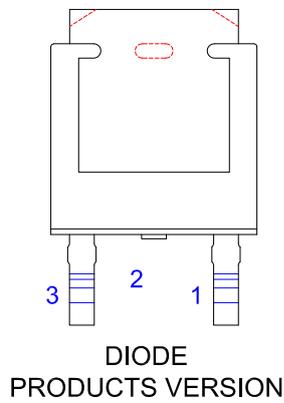
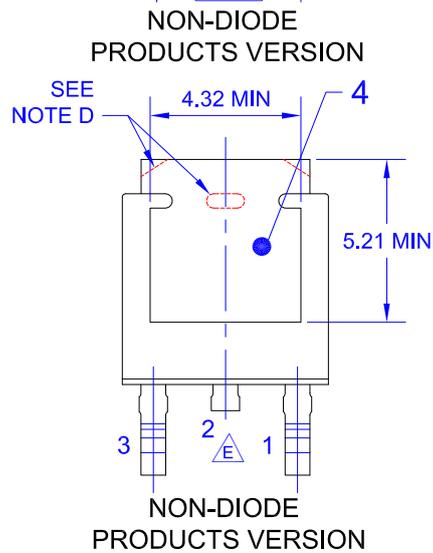
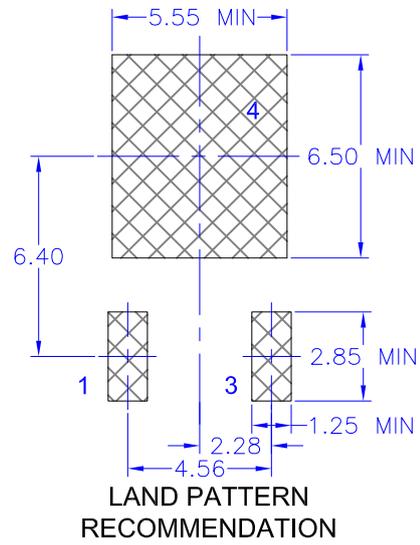
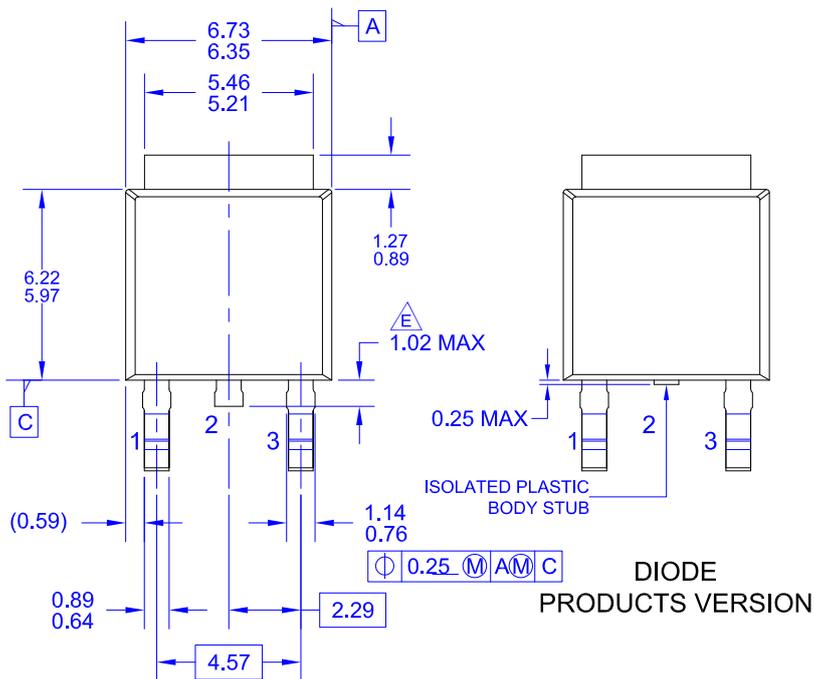
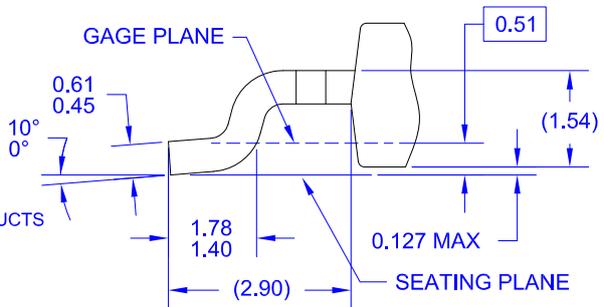


Figure 18. Total Gate Charge  $Q_{sync}$ . Test Circuit & Waveforms



**NOTES: UNLESS OTHERWISE SPECIFIED**

- A) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
- D) SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED CORNERS OR EDGE PROTRUSION.
- E) TRIMMED METAL CENTER LEAD IS PRESENT ON FOR NON-DIODE PRODUCTS
- F) DIMENSIONS ARE EXCLUSIVE OF BURS, MOLD FLASH AND TIE BAR EXTRUSIONS.
- G) LAND PATTERN RECOMMENDATION IS BASED ON IPC7351A STD TO228P991X239-3N.
- H) DRAWING NUMBER AND REVISION: MKT-TO252A03REV11



**DETAIL A**  
(ROTATED -90°)  
SCALE: 12X



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